FIG. 1

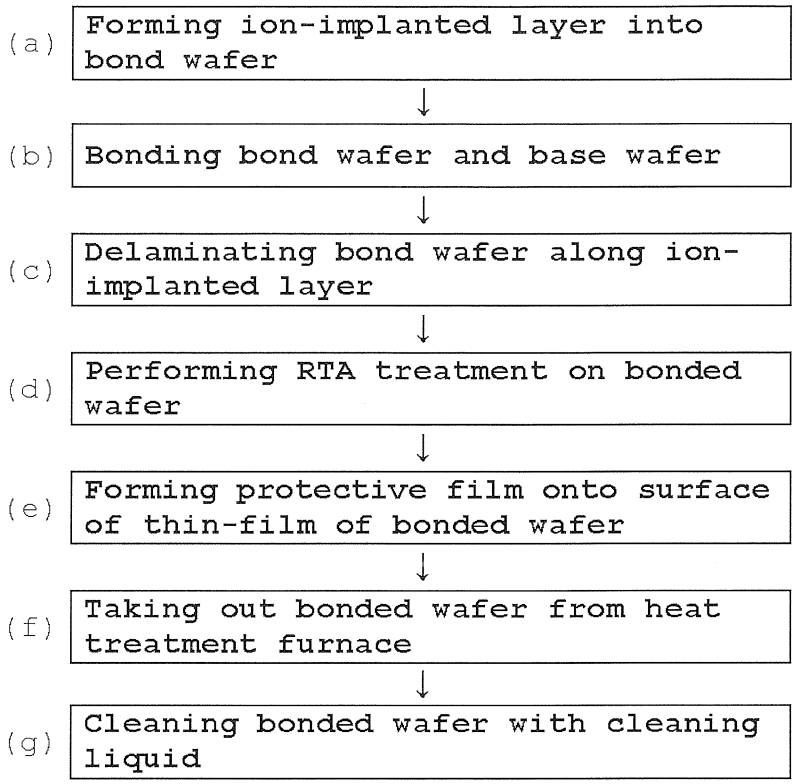

(a)
Forming ion-implanted layer into bond wafer
(b)
Bonding bond wafer and base wafer
(c)
Delaminating bond wafer along ion-implanted layer
(d)
Performing RTA treatment on bonded wafer
(e)
Forming protective film onto surface of thin-film of bonded wafer
(f)
Taking out bonded wafer from heat treatment furnace
(g)
Cleaning bonded wafer with cleaning liquid

FIG. 2

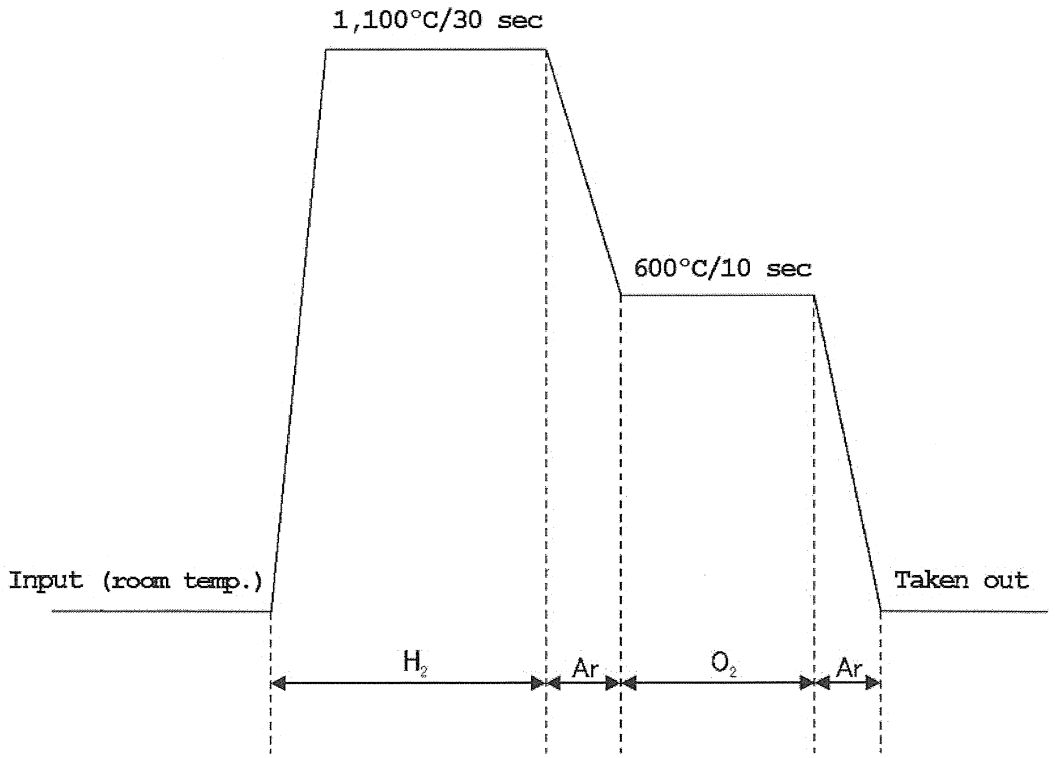

1,100°C/30 sec
600°C/10 sec
Input (room temp.)
Taken out
H2
Ar
O2
Ar

FIG. 3

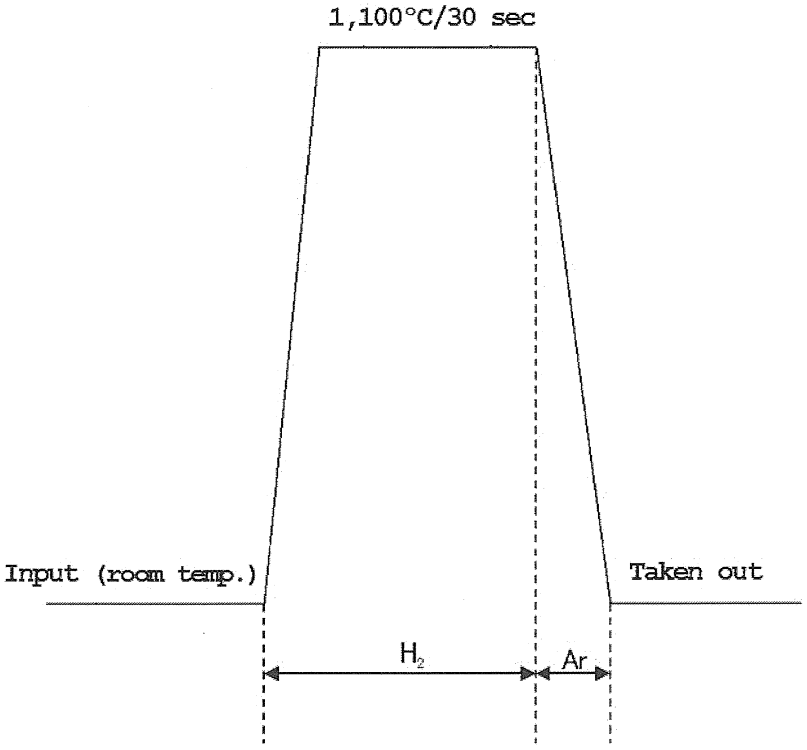


FIG. 4

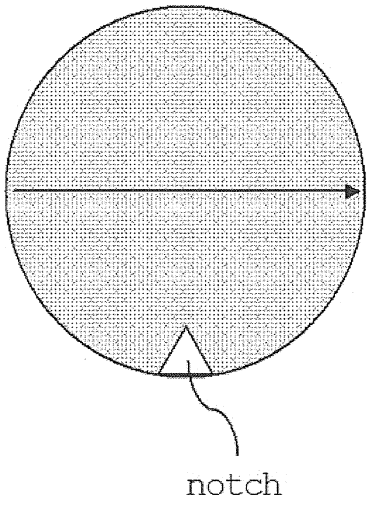
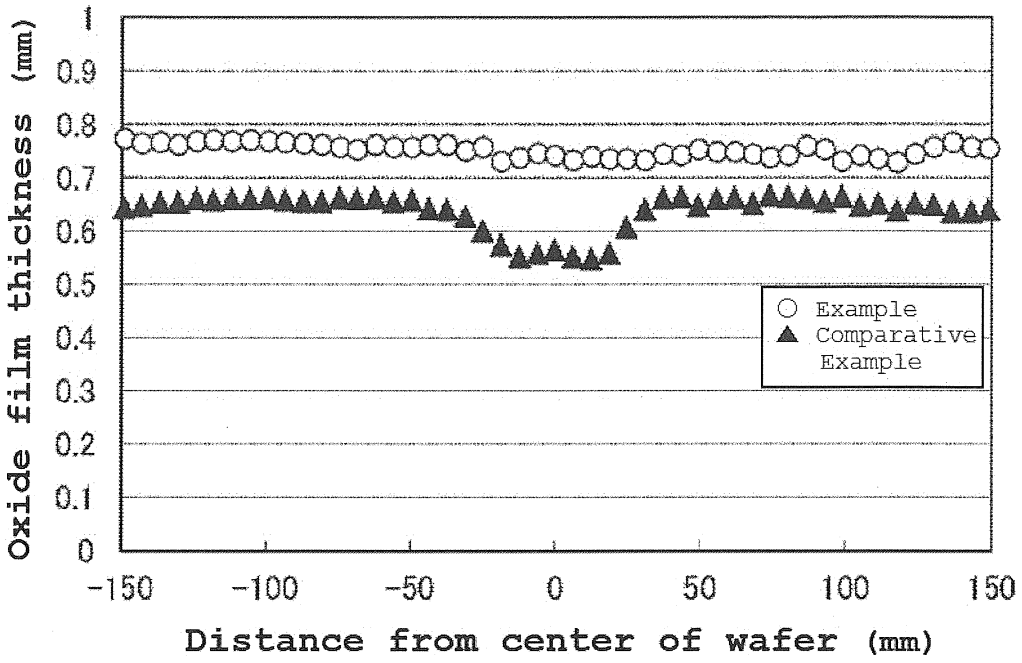


FIG. 5


Oxide film thickness (nm)
1
0.9
0.8
0.7
0.6
0.5
0.4
0.3
0.2
0.1
0
-150
-100
-50
0
50
100
150
Distance from center of wafer (mm)
Example
Comparative Example